PNP Epitaxial Planar Silicon Transistors NPN Triple Diffused Planar Silicon Transistors



2SB817/2SD1047

140V/12A AF 60W Output Applications

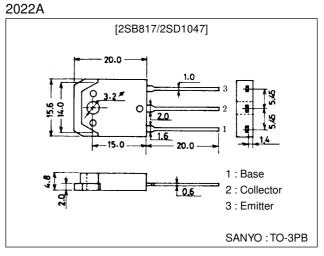
Features

- Capable of being mounted easily because of onepoint fixing type plastic molded package (Interchangeable with TO-3).
- \cdot Wide ASO because of on-chip ballast resistance.
- \cdot Good dependence of f_T on current and excellent high frequency responce.

The descriptions in parentheses are for the 2SB817 only : other descriptions than those in parentheses are common to the 2SB817 and 2SD1047.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)160	V
Collector-to-Emitter Voltage	V _{CEO}		()140	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	IC		(–)12	A
Collector Current (Pulse)	I _{CP}		(–)15	A
Collector Dissipation	PC	Tc=25°C	100	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-40 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)80V, I _E =0			(–)0.1	mA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)0.1	mA
DC Current Gain	h _{FE} 1	V _{CE} =(-)5V, I _C =(-)1A	60*		200*	
	h _{FE} 2	V _{CE} =(-)5V, I _C =(-)6A	20			
Gain-Bandwidth Product	fT	V _{CE} =(-)5V, I _C =(-)1A		15		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(300)		pF
				210		pF

* : The 2SB817/2SD1047 are classified by 1A h_{FE} as follows :

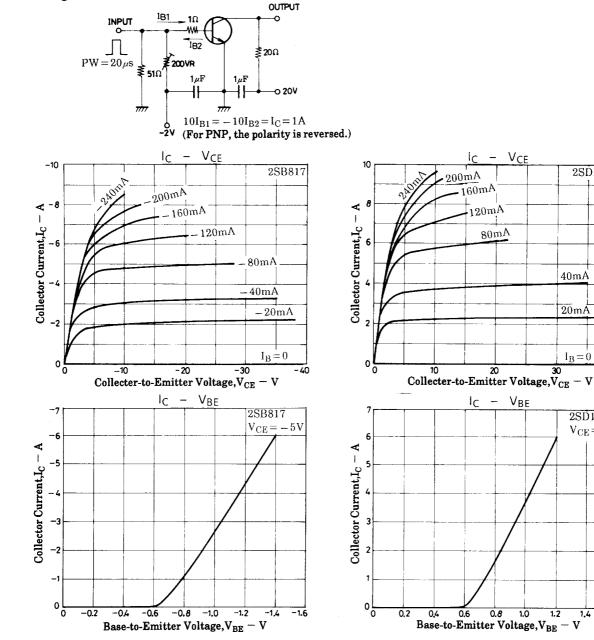
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Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Base-to-Emitter Voltage	V _{BE}	V _{CE} =(-)5V, I _C =(-)1A			1.5	V
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)5A, I _B =(-)0.5A		0.6	2.5	V
				(1.1)		V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)5mA, I _E =0	()160			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)5mA, R _{BE} =∞	()140			V
		I _C =(−)50mA, R _{BE} =∞	()140			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)5mA, I _C =0	()6			V
Turn-ON Time	ton	See specified Test Circuit		(0.25)		μs
				0.26		μs
Fall Time	t _f	See specified Test Circuit		(0.53)		μs
				0.68		μs
Storage Time	t _{stg}	See specified Test Circuit		(1.61)		μs
				6.88		μs

Switching Time Test Circuit



1.6

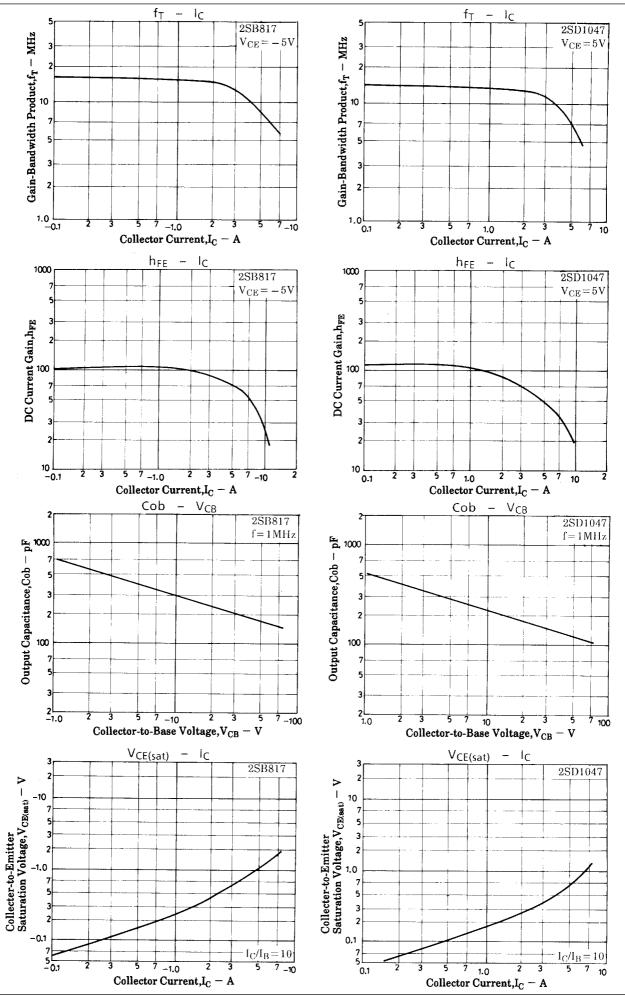
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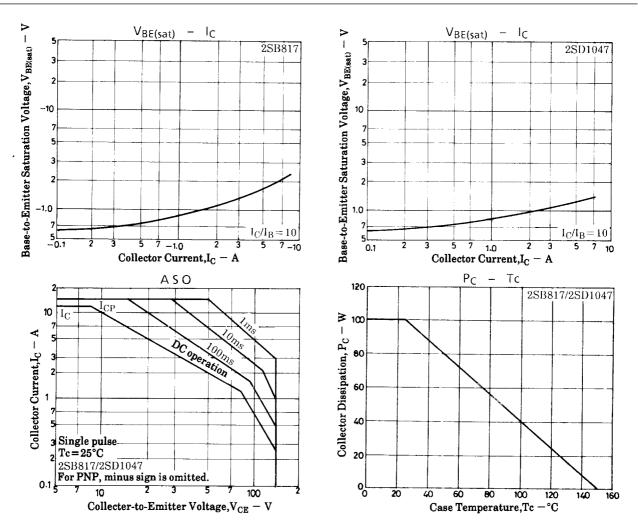
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2SD1047

 $V_{CE} = 5V$

2SB817/2SD1047





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